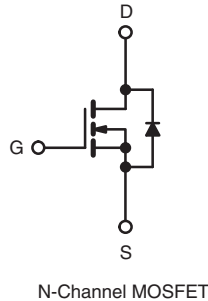
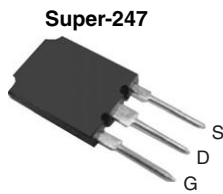


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.110
Q_g (Max.) (nC)	330	
Q_{gs} (nC)	84	
Q_{gd} (nC)	150	
Configuration	Single	



FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Enhanced Body Diode dV/dt Capability
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT

APPLICATIONS

- Hard Switching Primary or PFC Switch
- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Motor Drive

ORDERING INFORMATION	
Package	Super-247
Lead (Pb)-free	IRFPS40N60KPbF
	SiHFPS40N60K-E3
SnPb	IRFPS40N60K
	SiHFPS40N60K


ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	I_D	$T_C = 25^\circ\text{C}$	40
			$T_C = 100^\circ\text{C}$	
Pulsed Drain Current ^a		I_{DM}	160	A
Linear Derating Factor			4.5	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^b		E_{AS}	600	mJ
Repetitive Avalanche Current ^a		I_{AR}	40	A
Repetitive Avalanche Energy ^a		E_{AR}	57	mJ
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	570	W
Peak Diode Recovery dV/dt^c		dV/dt	7.5	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25^\circ\text{C}$, $L = 0.84$ mH, $R_g = 25 \Omega$, $I_{AS} = 38$ A, $dV/dt = 5.5$ V/ns (see fig. 12a).
- $I_{SD} \leq 38$ A, $dI/dt \leq 150$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.22	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.63	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	50	μA	
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 24\text{ A}^b$	-	0.110	0.130	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 24\text{ A}^b$	21	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	7970	-	pF	
Output Capacitance	C_{oss}		-	750	-		
Reverse Transfer Capacitance	C_{rss}		-	75	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	9440	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 480\text{ V}, f = 1.0\text{ MHz}$	-	200	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 0\text{ V to } 480\text{ V}^c$	-	260	-	
Gate-Source Charge	Q_{gs}		$I_D = 38\text{ A}, V_{DS} = 480\text{ V}$, see fig. 6 and 13 ^b	-	-	330	nC
Gate-Drain Charge	Q_{gd}			-	-	84	
Turn-On Delay Time	$t_{d(on)}$			-	-	150	
Rise Time	t_r		$V_{DD} = 300\text{ V}, I_D = 38\text{ A}, R_G = 4.3\text{ }\Omega$, see fig. 10 ^b	-	47	-	ns
Turn-Off Delay Time	$t_{d(off)}$	-		110	-		
Fall Time	t_f	-		97	-		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	40	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	160		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 38\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$	$I_F = 38\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	630	950	ns
		$T_J = 125\text{ }^\circ\text{C}$		-	730	1090	
Body Diode Reverse Recovery Charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$		-	14	20	μC
		$T_J = 125\text{ }^\circ\text{C}$		-	17	25	
Body Diode Recovery Current	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	-	39	58	A	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

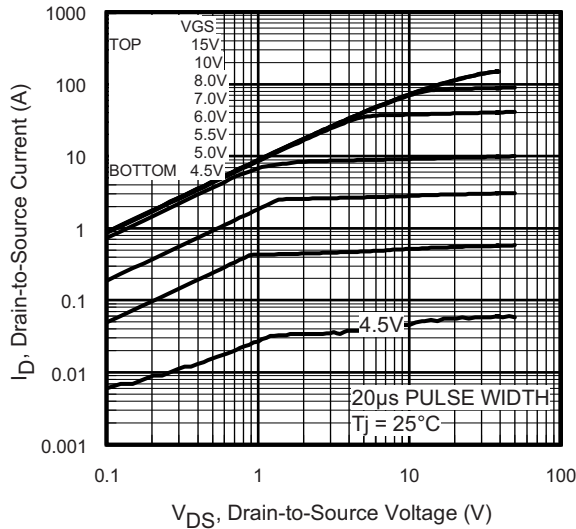


Fig. 1 - Typical Output Characteristics

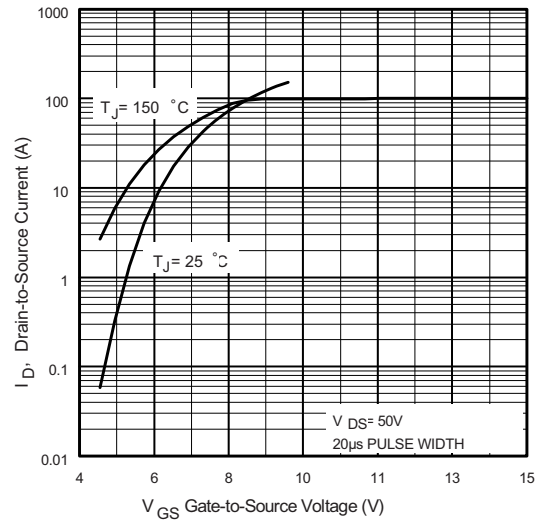


Fig. 3 - Typical Transfer Characteristics

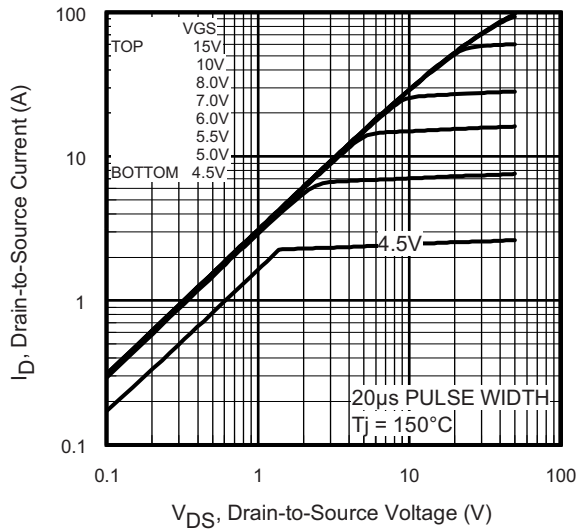


Fig. 2 - Typical Output Characteristics

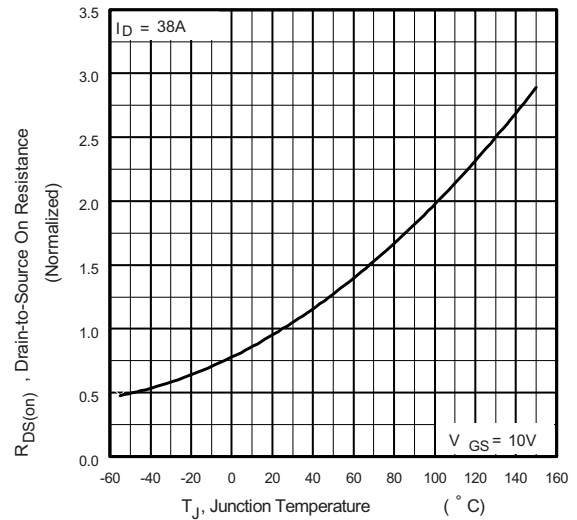


Fig. 4 - Normalized On-Resistance vs. Temperature

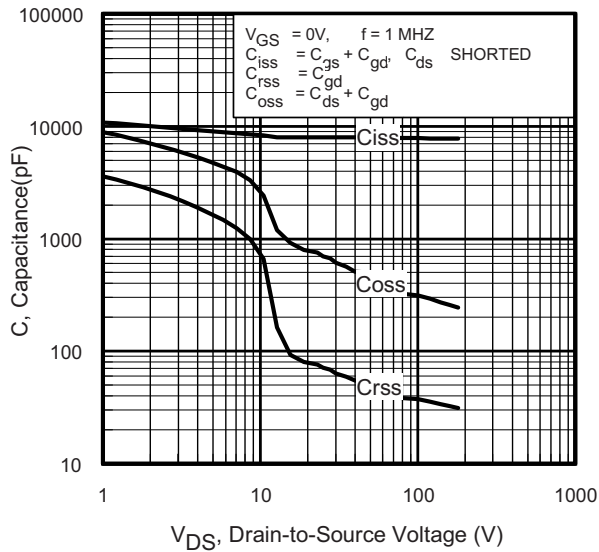


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

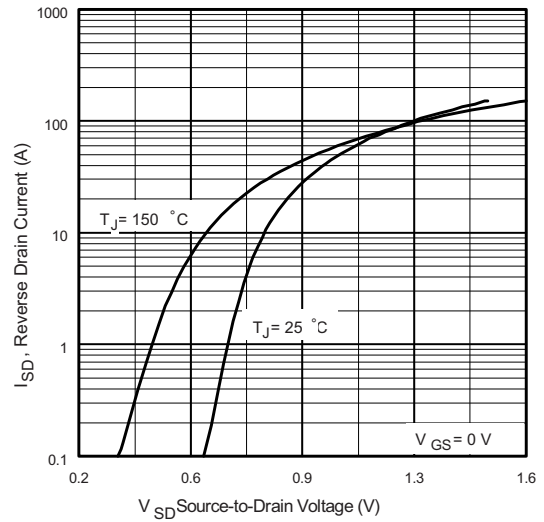


Fig. 7 - Typical Source-Drain Diode Forward Voltage

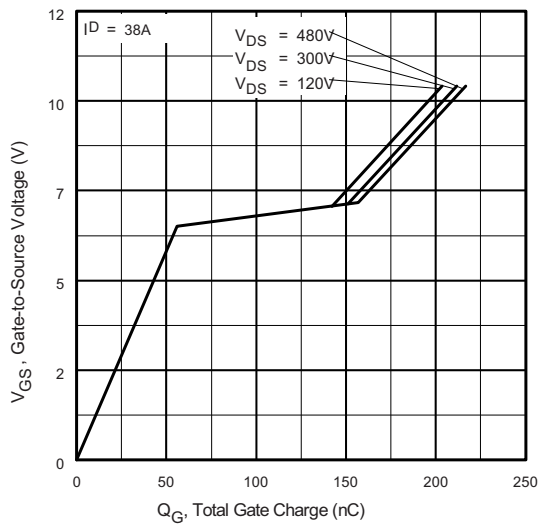


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

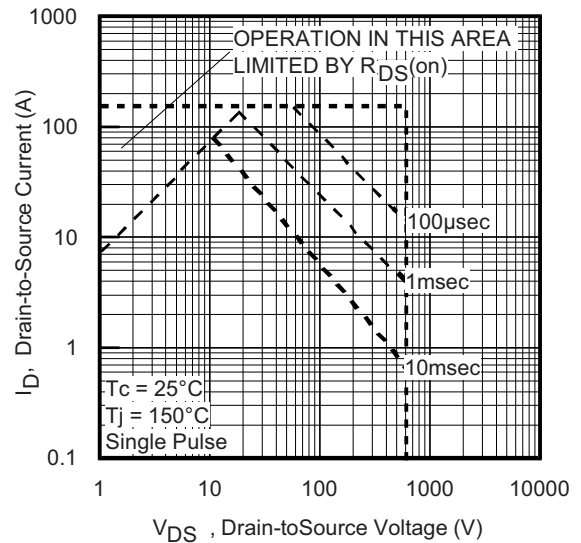


Fig. 8 - Maximum Safe Operating Area

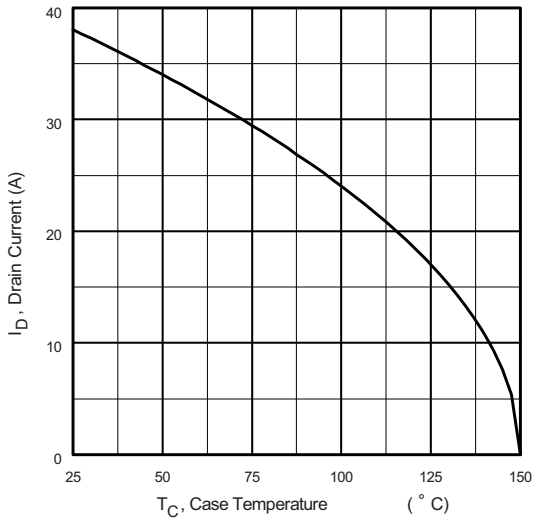


Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

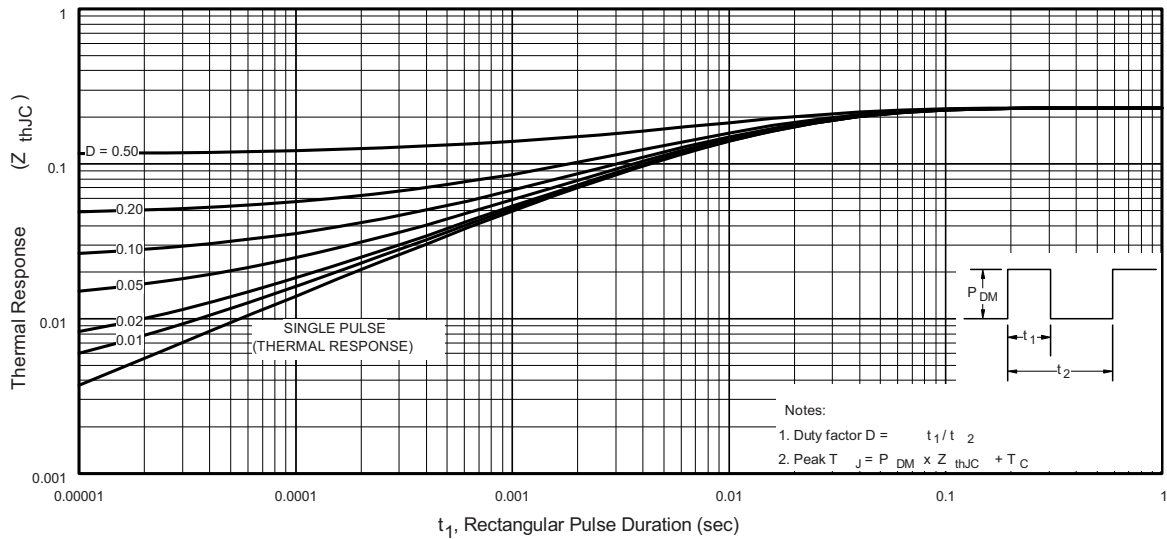


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

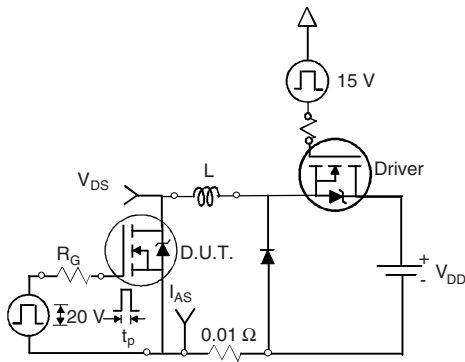


Fig. 12a - Unclamped Inductive Test Circuit

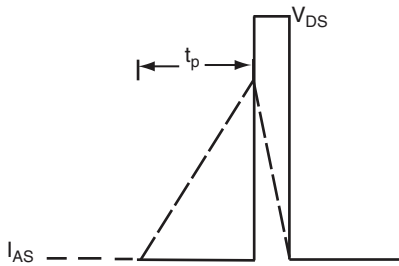


Fig. 12b - Unclamped Inductive Waveforms

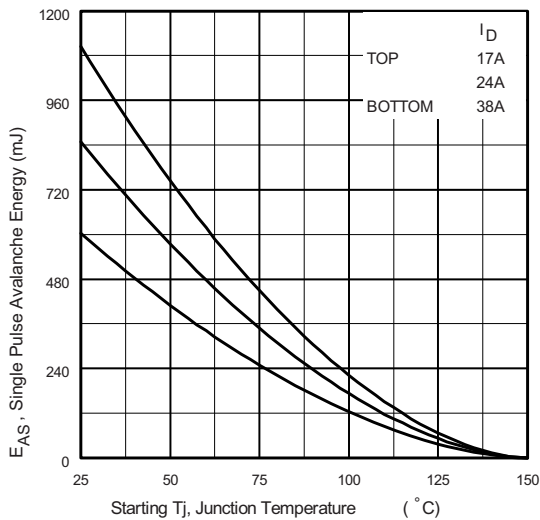


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

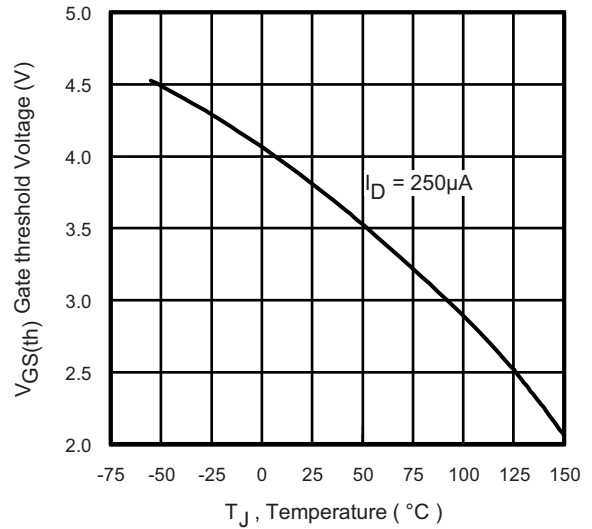


Fig. 12d - Threshold Voltage vs. Temperature

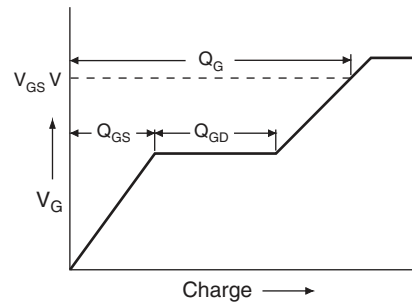


Fig. 13a - Basic Gate Charge Waveform

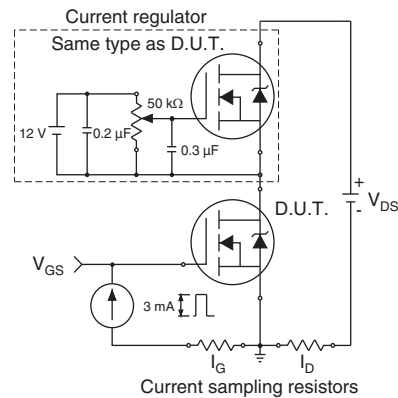
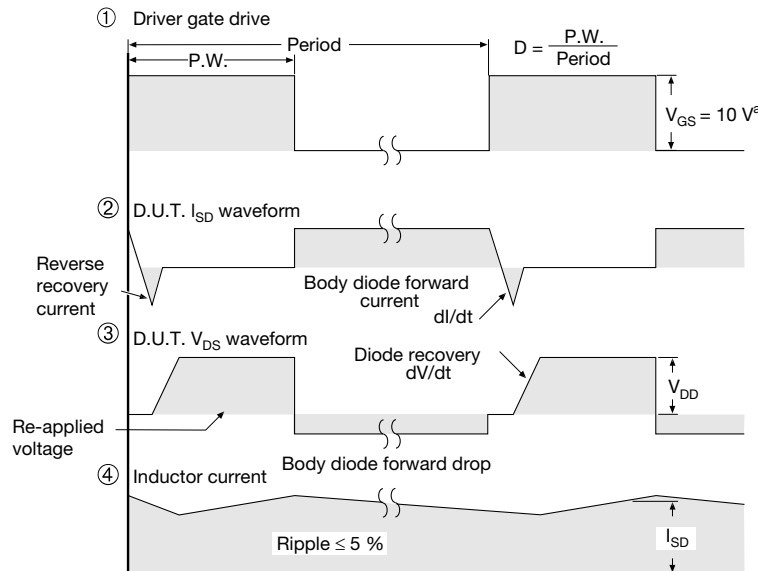


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



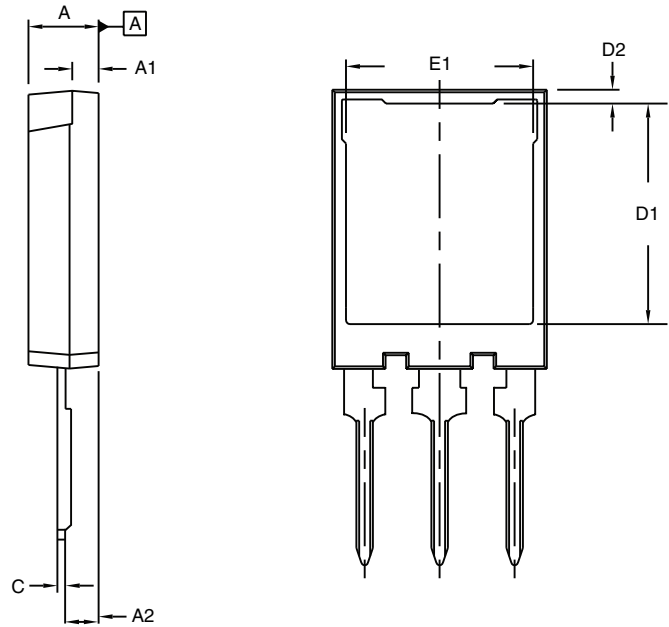
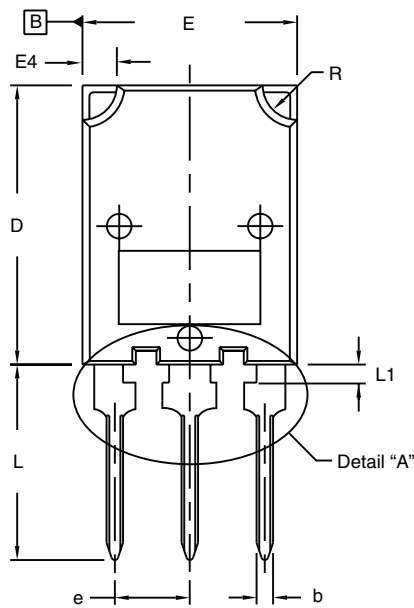
Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

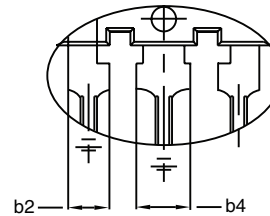
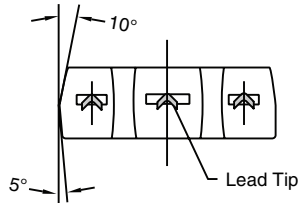
Fig. 14 - For N-Channel

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TO-274AA (HIGH VOLTAGE)



⊕ 0.10 (0.25) ⊕ B A ⊕



Detail "A"
Scale: 2:1

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c	0.80	1.20	0.031	0.047
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

ECN: S-82247-Rev. A, 06-Oct-08
DWG: 5975

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body.
3. Outline conforms to JEDEC outline to TO-274AA.



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